



TM10P06MSI

P-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

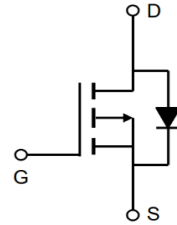
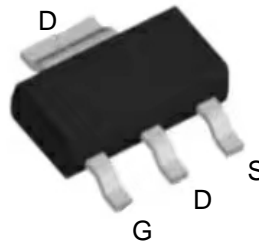
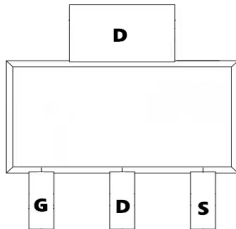
General Features

 $V_{DS} = -60V$ $I_D = -10A$ $R_{DS(ON)} = 70m\Omega$ (typ.) @ $V_{GS} = -10V$

100% UIS Tested

100% R_g Tested

MSI:SOT-223-3L



Marking:10P06

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-10	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-6.7	A
I_{DM}	Pulsed Drain Current ²	-34.4	A
EAS	Single Pulse Avalanche Energy ³	29.8	mJ
I_{AS}	Avalanche Current	24.4	A
$P_D @ T_C = 25^\circ C$	Total Power Dissipation ⁴	31.3	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	62	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	4	$^\circ C/W$

P-Channel Electrical Characteristics ($T_J=25\text{ }^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=-1\text{mA}$	---	-0.023	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=-10V, I_D=-10A$	---	70	87	m Ω
		$V_{GS}=-4.5V, I_D=-5A$	---	88	99	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250\mu A$	-1.0	-1.6	-2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.65	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=-48V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=-48V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
gfs	Forward Transconductance	$V_{DS}=-5V, I_D=-4A$	---	8.7	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	15	---	Ω
Q_g	Total Gate Charge (-4.5V)	$V_{DS}=-12V, V_{GS}=-4.5V, I_D=-6A$	---	11.8	---	nC
Q_{gs}	Gate-Source Charge		---	1.9	---	
Q_{gd}	Gate-Drain Charge		---	6.5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=-15V, V_{GS}=-10V, R_G=3.3\Omega, I_D=-1A$	---	8.8	---	ns
T_r	Rise Time		---	19.6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	47.2	---	
T_f	Fall Time		---	9.6	---	
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V, f=1\text{MHz}$	---	1880	---	pF
C_{oss}	Output Capacitance		---	73	---	
C_{rss}	Reverse Transfer Capacitance		---	50	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,5}	$V_G=V_D=0V$, Force Current	---	---	-10	A
I_{SM}	Pulsed Source Current ^{2,5}		---	---	-20	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=-1A, T_J=25^\circ\text{C}$	---	---	-1	V

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is $V_{DD}=-25V, V_{GS}=-10V, L=0.1\text{mH}, I_{AS}=-24.4A$
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



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P-Channel Typical Characteristics

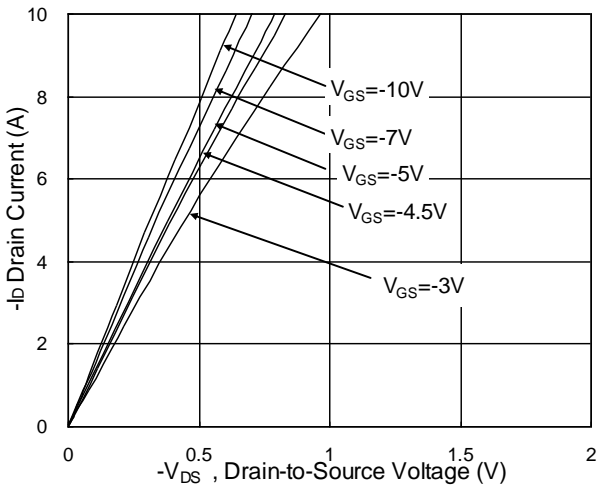


Fig.1 Typical Output Characteristics

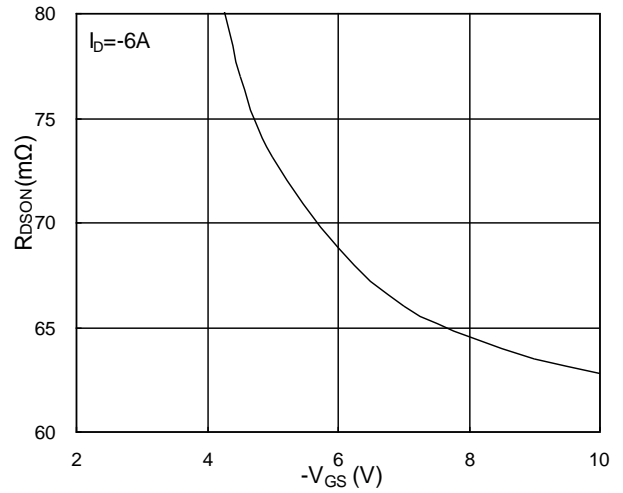


Fig.2 On-Resistance v.s Gate-Source

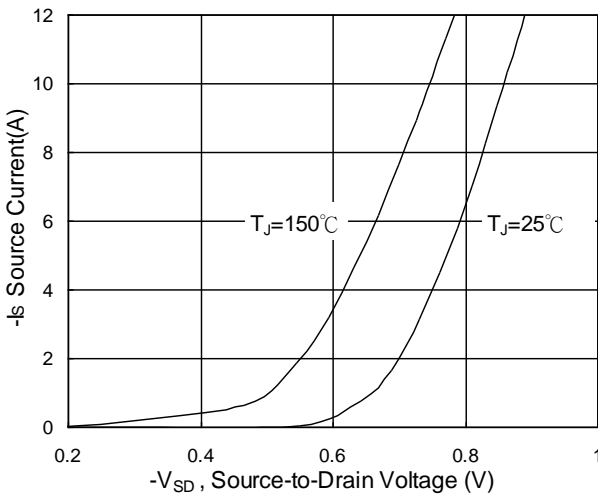


Fig.3 Forward Characteristics of Reverse

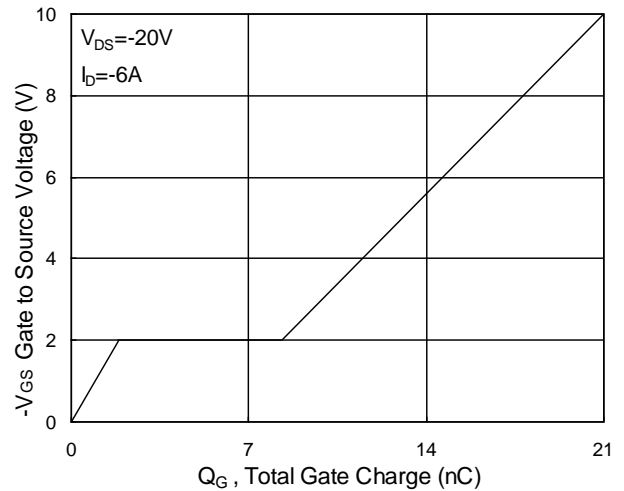


Fig.4 Gate-Charge Characteristics

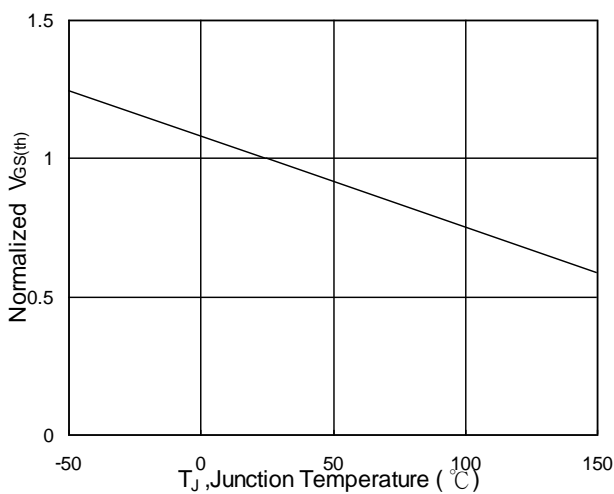


Fig.5 Normalized $V_{GS(th)}$ v.s T_J

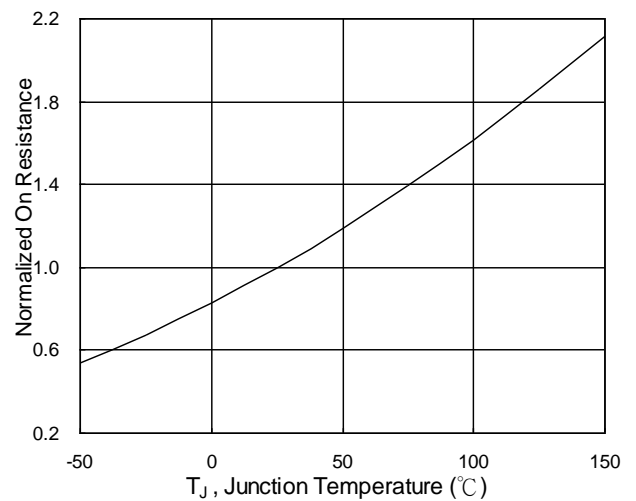


Fig.6 Normalized $R_{DS(on)}$ v.s T_J

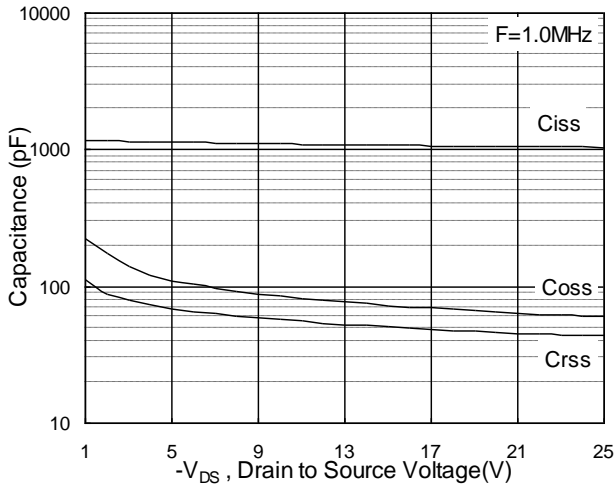


Fig.7 Capacitance

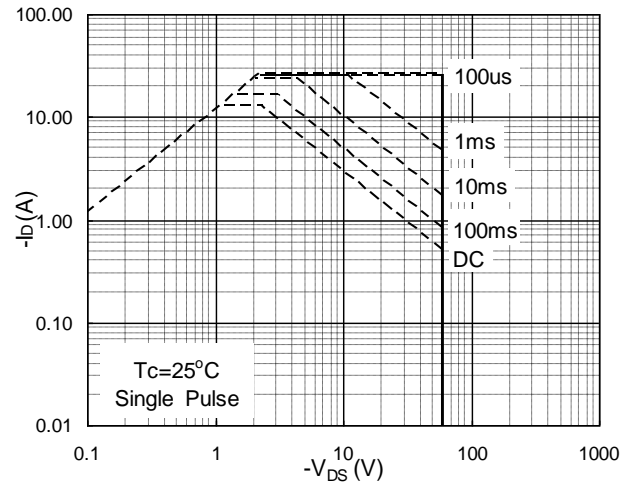


Fig.8 Safe Operating Area

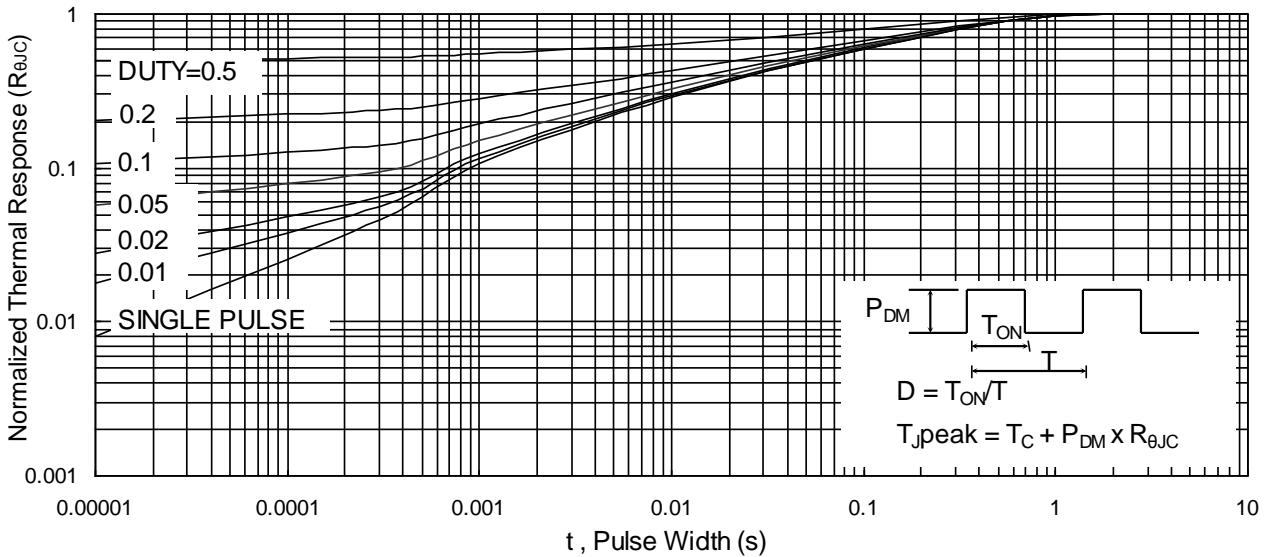


Fig.9 Normalized Maximum Transient Thermal Impedance

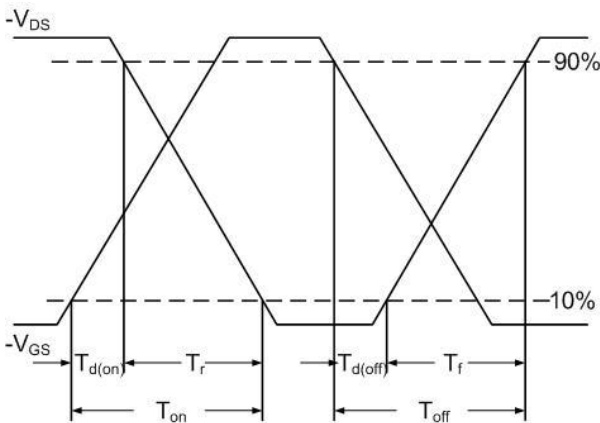


Fig.10 Switching Time Waveform

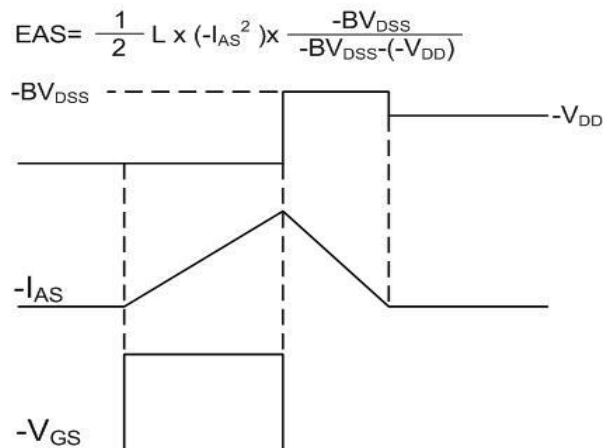
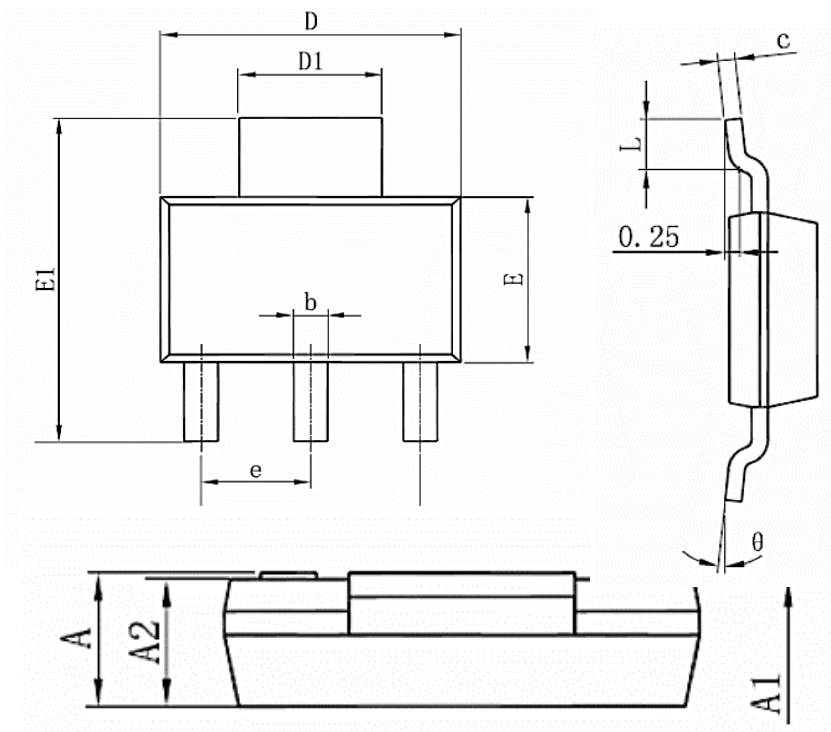


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data:SOT-223-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.52	1.8	0.06	0.049
A1	0.000	0.100	0.000	0.004
A2	1.5	1.7	0.059	0.045
b	0.66	0.82	0.026	0.032
c	0.25	0.35	0.010	0.014
D	6.2	6.4	0.244	0.252
D1	2.9	3.1	0.114	0.122
E	3.3	3.7	0.130	0.146
E1	6.83	7.07	0.269	0.278
e	2.300(BSC)		0.037(BSC)	
e1	4.500	4.700	0.177	0.185
L	0.900	1.15	0.035	0.045
θ	0°	10°	0°	10°